



## PE4614 N and P Channel Enhancement Mode Power MOSFET

### PE4614 Description

The PE4614 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. It can be used in a wide variety of applications.

### PE4614 General Features

- N-Channel
- $V_{DS} = 40V$ ,  $I_D = 8A$

$R_{DS(ON)} < 19m\Omega$  @  $V_{GS}=10V$

$R_{DS(ON)} < 28m\Omega$  @  $V_{GS}=4.5V$

- P-Channel

- $V_{DS} = -40V$ ,  $I_D = -7A$

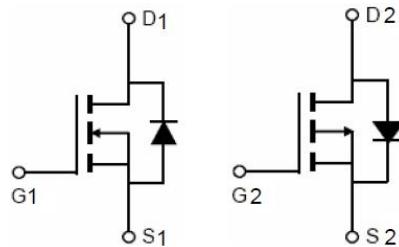
$R_{DS(ON)} < 35m\Omega$  @  $V_{GS}=-10V$

$R_{DS(ON)} < 45m\Omega$  @  $V_{GS}=-4.5V$

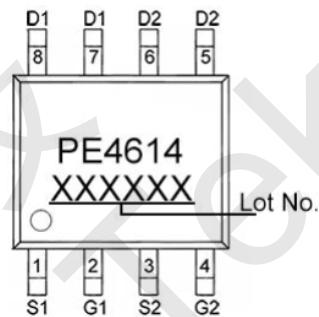
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

### PE4614 Application

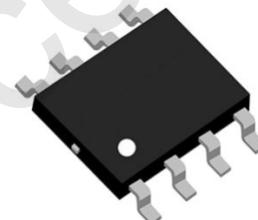
- DC motor
- PWM applications



Schematic diagram



Marking and pin assignment



SOP-8

### PE4614 Absolute Maximum Ratings ( $TA=25^\circ C$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	$V_{DS}$	40	-40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Drain Current-Continuous	$I_D$	8	-7	A
Pulsed Drain Current (Note 1)	$I_{DM}$	32	-28	A
Maximum Power Dissipation	$P_D$	2	2	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150		°C

### PE4614 Thermal Characteristic

Parameter	Symbol	N-Channel	P-Channel	Unit
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	62.5	62.5	°C/W



**PE4614 N-Channel Electrical Characteristics (TA=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=8A$	-	15	19	$m\Omega$
		$V_{GS}=4.5V, I_D=7A$	-	20	28	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=8A$	-	25	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=20V, V_{GS}=0V, F=1.0MHz$	-	1160	-	pF
Output Capacitance	$C_{oss}$		-	110	-	pF
Reverse Transfer Capacitance (Note 4)	$C_{rss}$		-	100	-	pF
<b>Switching Characteristics</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=2A, R_L=1\Omega, V_{GS}=10V, R_G=3\Omega$	-	5.5	-	nS
Turn-on Rise Time	$t_r$		-	14	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	22	-	nS
Turn-Off Fall Time	$t_f$		-	9	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=20V, I_D=8A, V_{GS}=10V$	-	23	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.5	-	nC
Gate-Drain Charge	$Q_{gd}$		-	5.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	3	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to product.



### PE4614 Typical Electrical and Thermal Characteristics

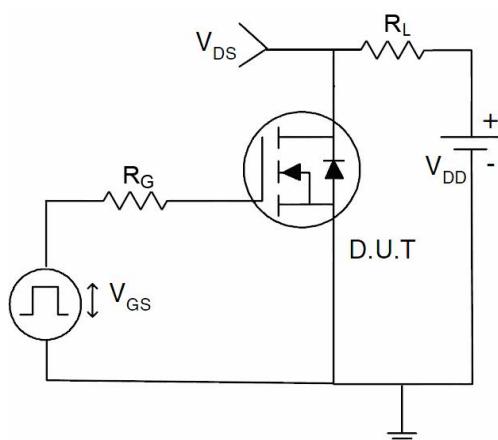


Figure 1 Switching Test Circuit

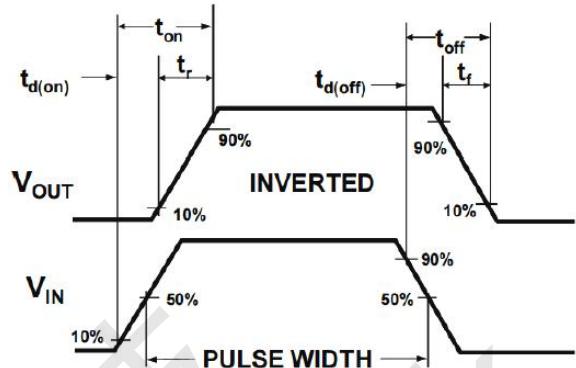


Figure 2 Switching Waveform

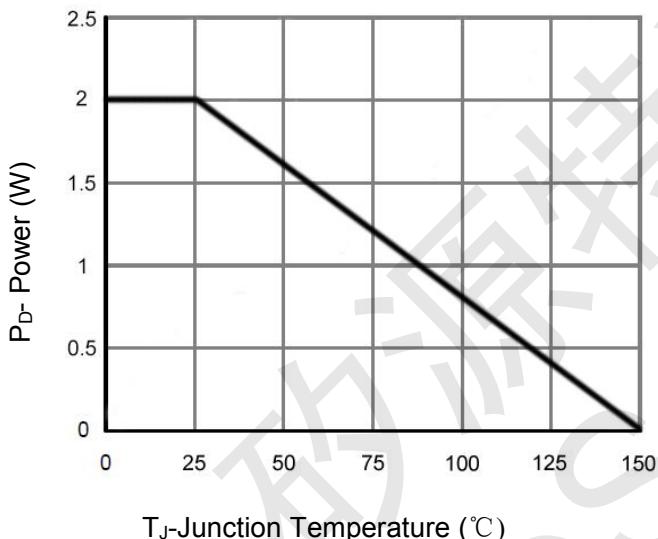


Figure 3 Power De-rating

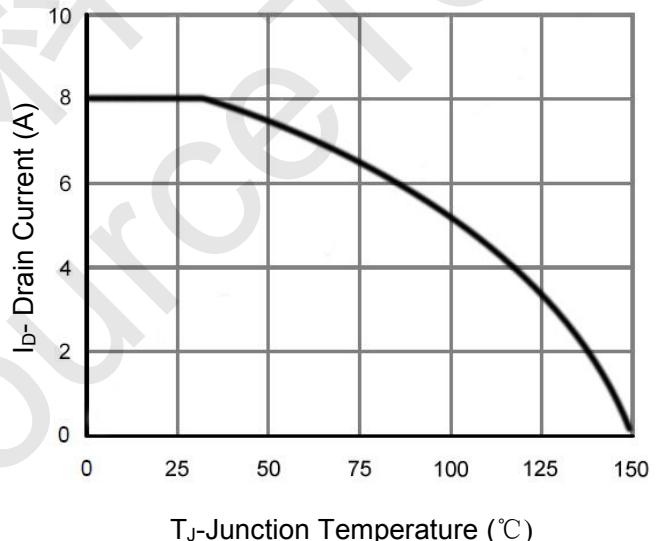


Figure 4 Drain Current

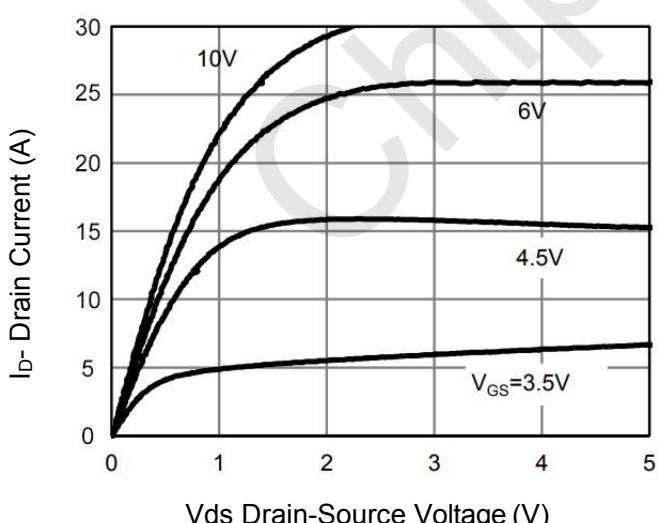


Figure 5 Output Characteristics

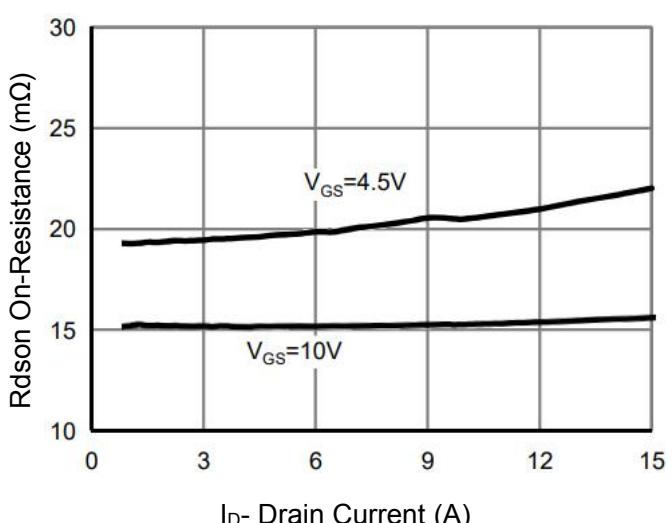


Figure 6 Rdson vs Drain Current

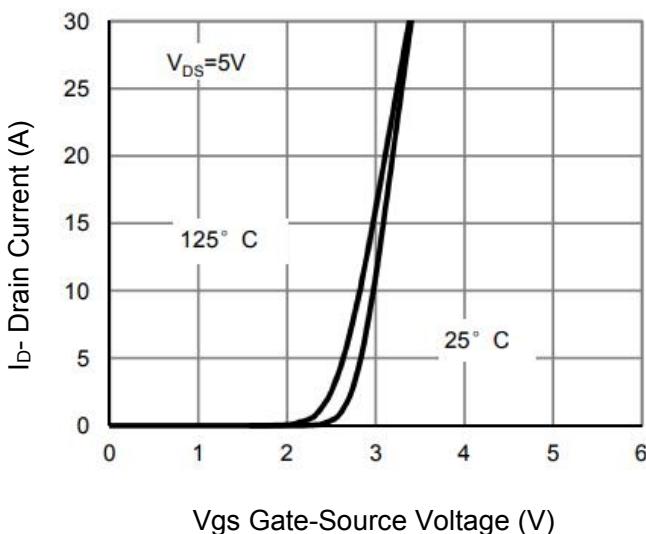


Figure 7 Transfer Characteristics

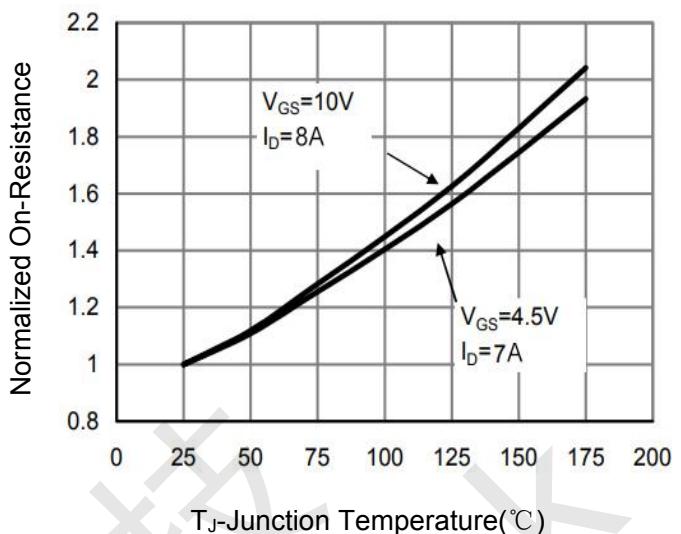


Figure 8  $R_{DSON}$  vs Junction Temperature

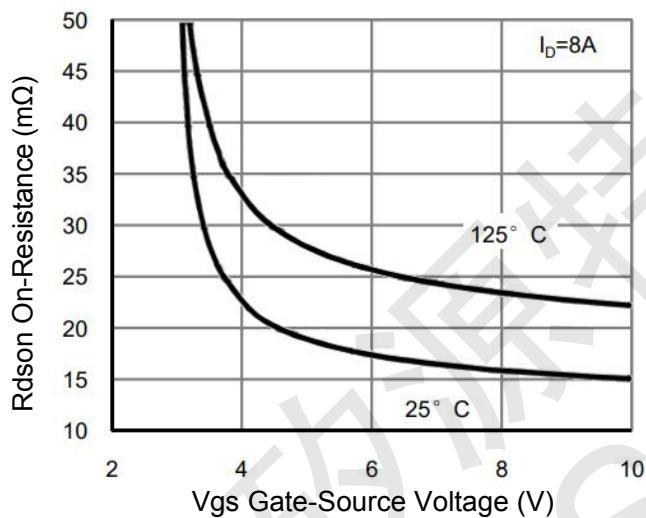


Figure 9  $R_{DSON}$  vs  $V_{GS}$

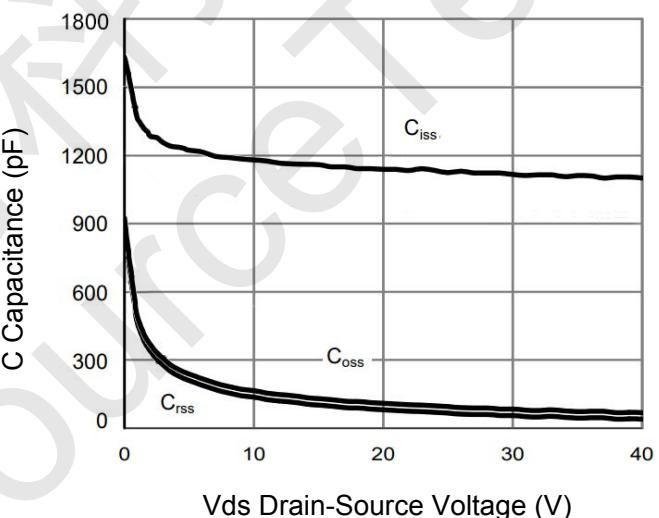


Figure 10 Capacitance vs  $V_{DS}$

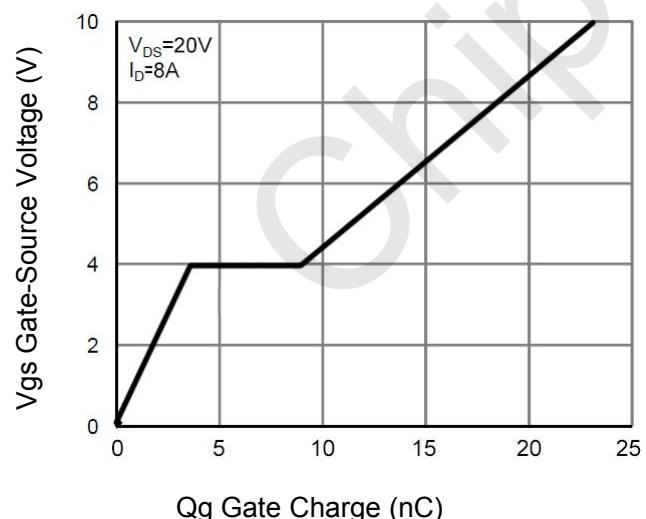


Figure 11 Gate Charge

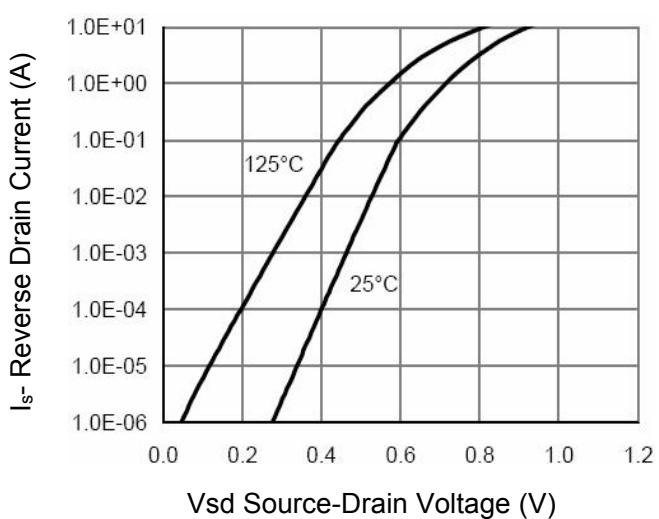
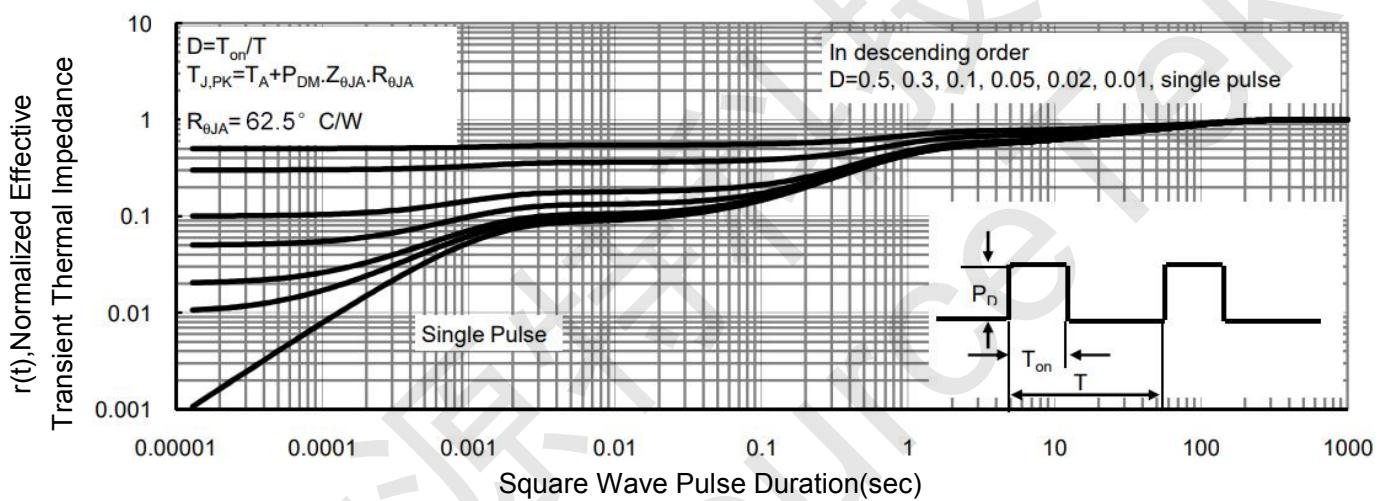
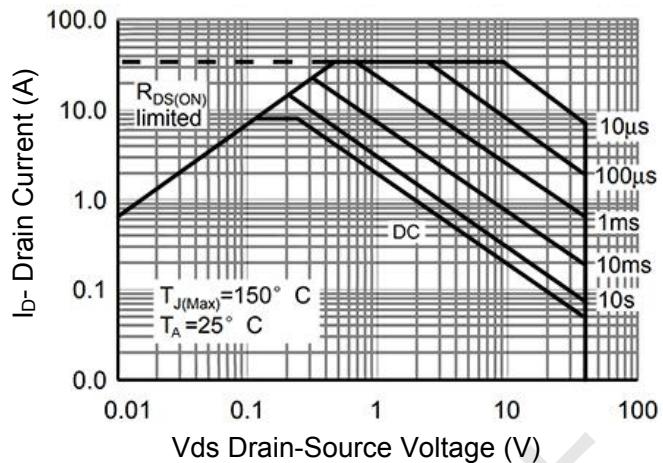


Figure 12 Source-Drain Diode Forward





**PE4614 P-Channel Electrical Characteristics (TC=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-40V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.5	-2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-7A$	-	27	35	$m\Omega$
		$V_{GS}=-4.5V, I_D=-6A$	-	37	45	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-10V, I_D=-6A$	-	23	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=-20V, V_{GS}=0V, F=1.0MHz$	-	1250	-	pF
Output Capacitance	$C_{oss}$		-	120	-	pF
Reverse Transfer Capacitance (Note 4)	$C_{rss}$		-	105	-	pF
<b>Switching Characteristics</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=1\Omega, V_{GS}=-10V, R_G=3\Omega$	-	10	-	nS
Turn-on Rise Time	$t_r$		-	18	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	38	-	nS
Turn-Off Fall Time	$t_f$		-	24	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-20V, I_D=-6A, V_{GS}=-10V$	-	28	-	nC
Gate-Source Charge	$Q_{gs}$		-	4.5	-	nC
Gate-Drain Charge	$Q_{gd}$		-	8	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_s=-1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	$I_s$		-	-	-3	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
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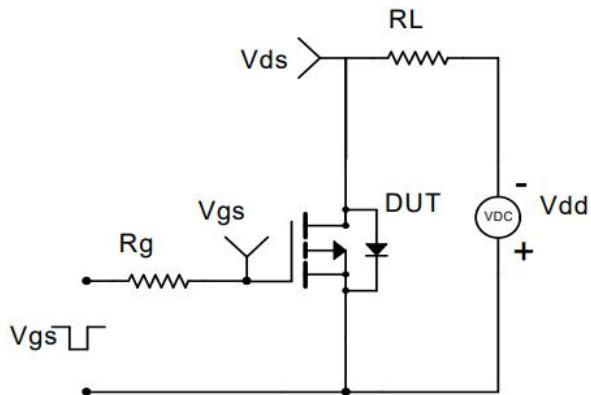
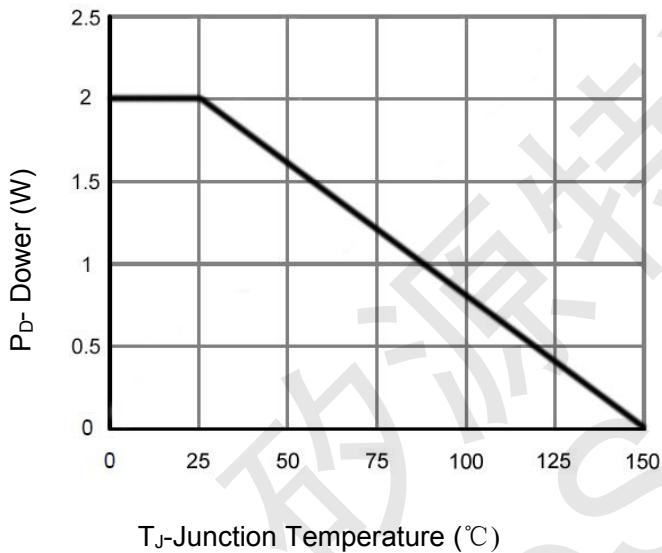
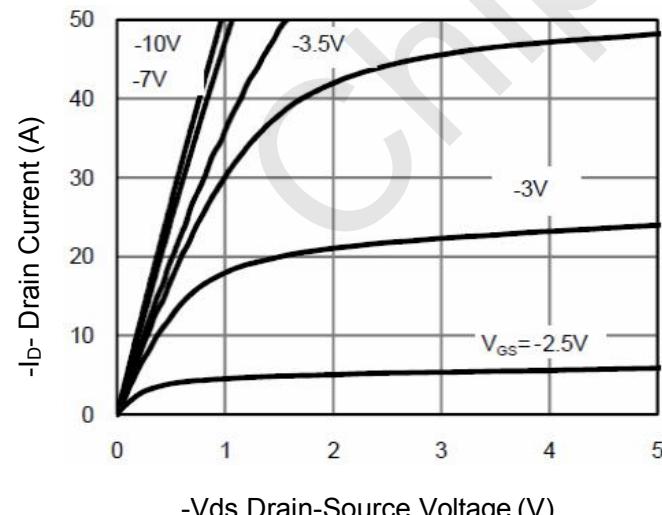


Figure 1 Switching Test Circuit



T<sub>j</sub>-Junction Temperature (°C)

Figure 3 Power De-rating



-V<sub>DS</sub> Drain-Source Voltage (V)

Figure 5 Output Characteristics

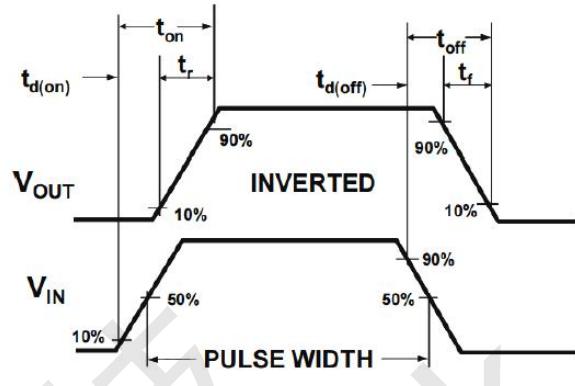
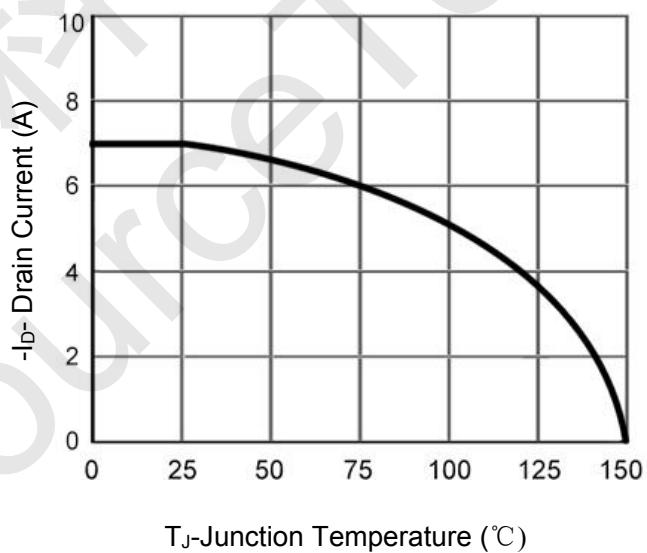
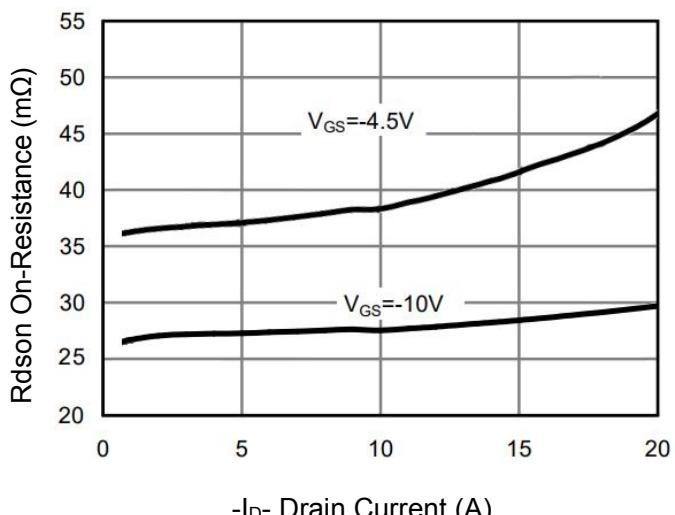


Figure 2 Switching Waveform



T<sub>j</sub>-Junction Temperature (°C)

Figure 4 Drain Current



-I<sub>D</sub>- Drain Current (A)

Figure 6 Rdson vs Drain Current

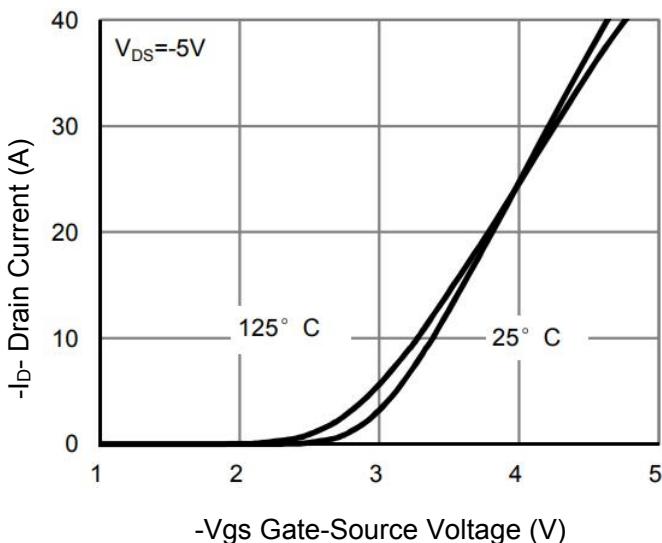


Figure 7 Transfer Characteristics

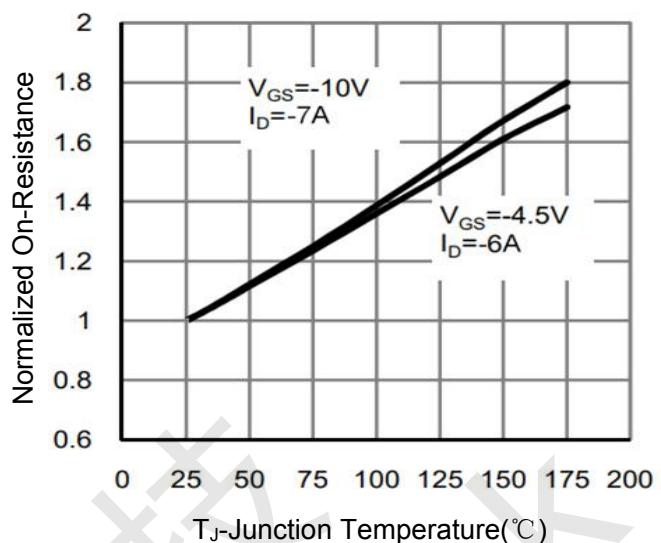


Figure 8  $R_{DSON}$  vs Junction Temperature

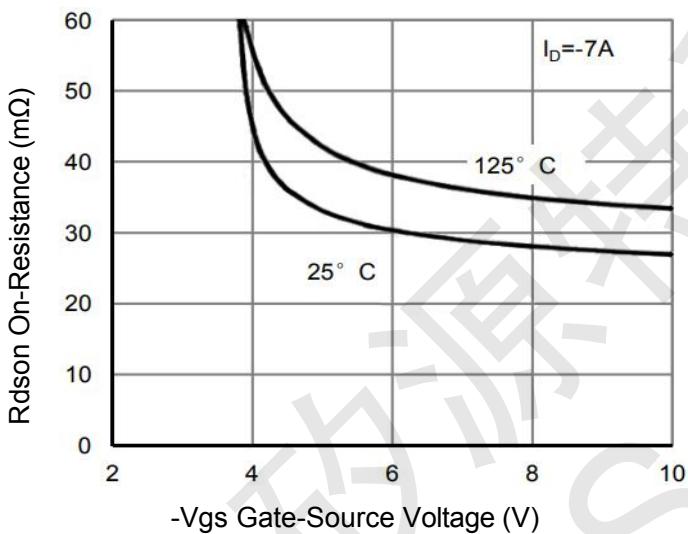


Figure 9  $R_{DSON}$  vs  $V_{GS}$

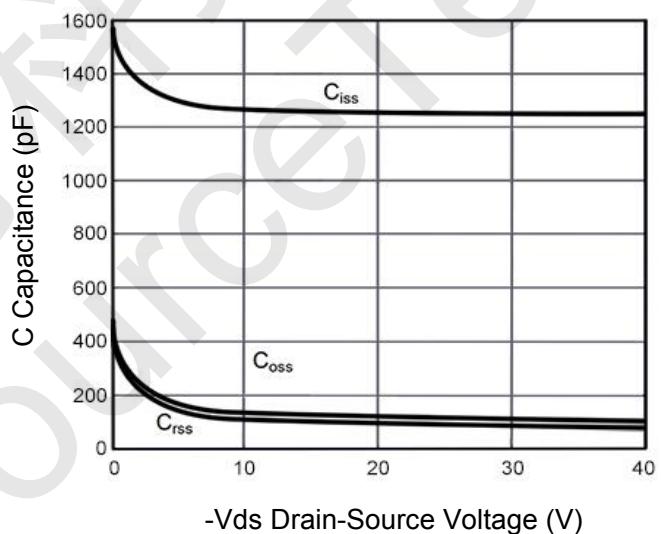


Figure 10 Capacitance vs  $V_{DS}$

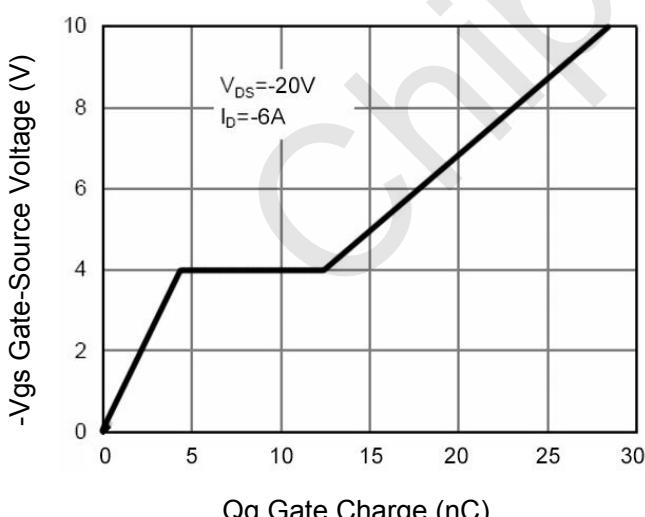


Figure 11 Gate Charge

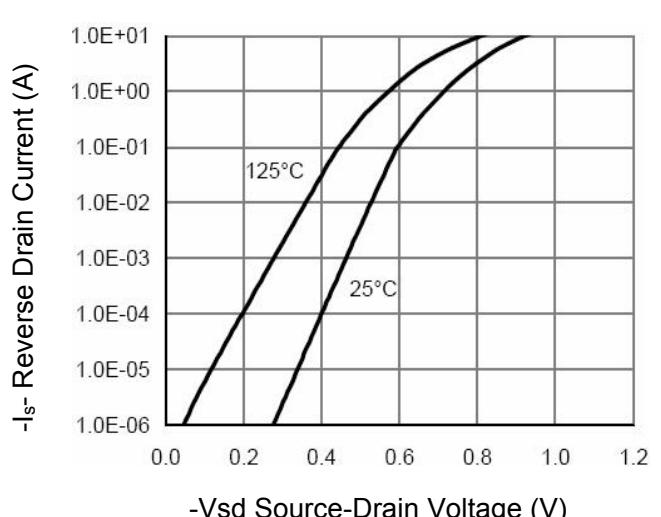


Figure 12 Source-Drain Diode Forward

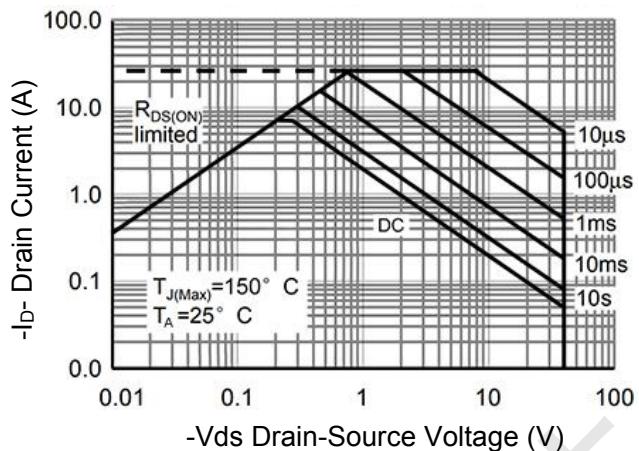


Figure 13 Safe Operation Area

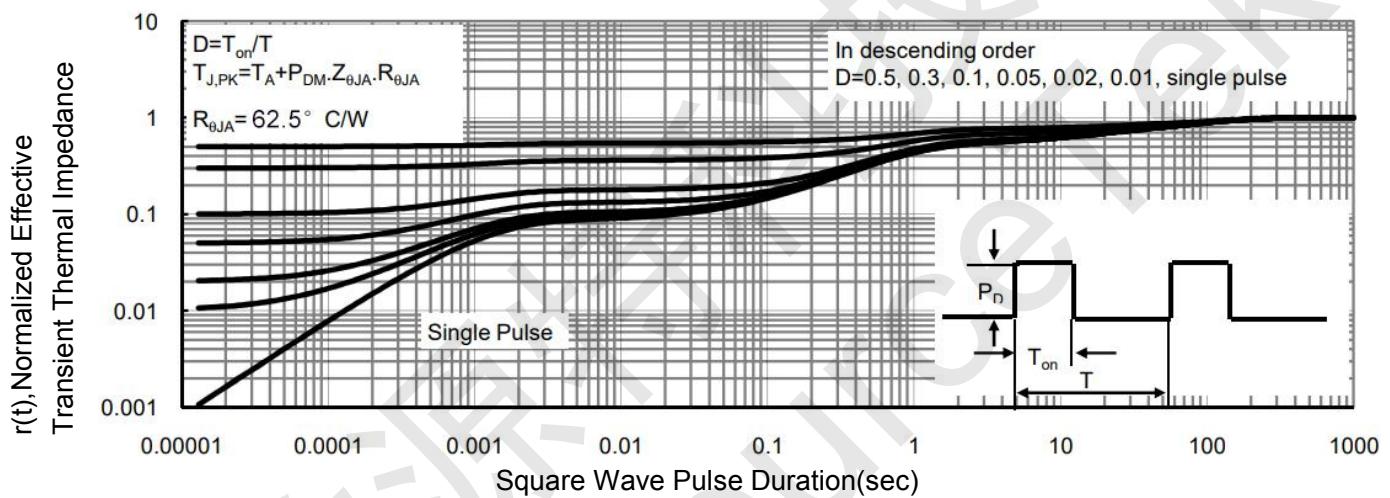
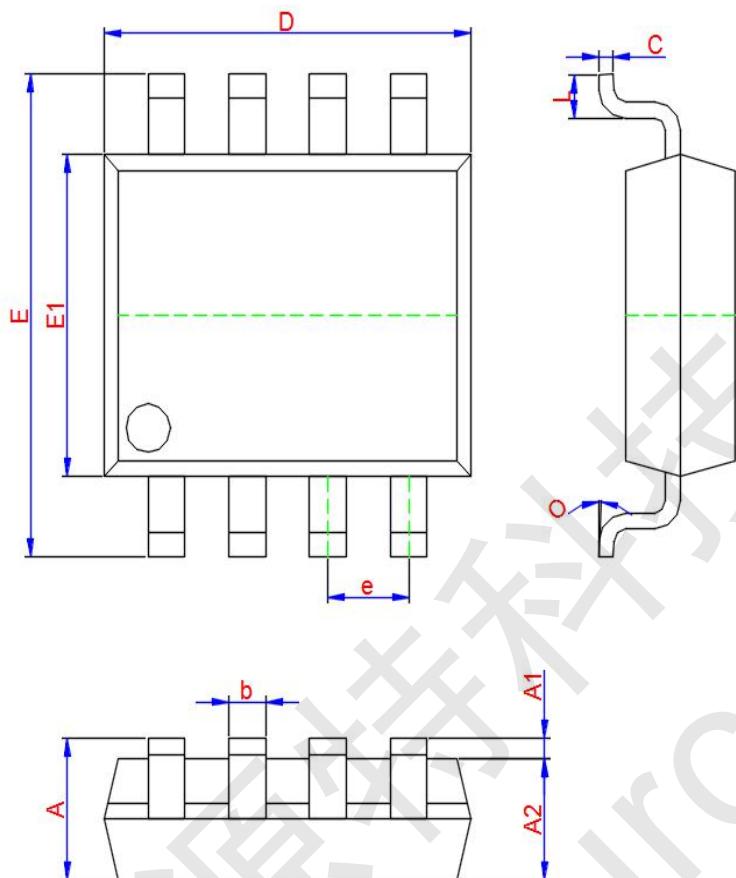


Figure 14 Normalized Maximum Transient Thermal Impedance



PE4614 SOP-8 Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	1.350	1.550	1.750
A1	0.100	0.175	0.250
A2	1.350	1.450	1.550
b	0.330	0.420	0.510
c	0.170	0.210	0.250
D	4.700	4.900	5.100
e	1.270 TYP.		
E	5.800	6.000	6.200
E1	3.750	3.900	4.050
L	0.400	0.835	1.270
O	0°	4°	8°